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Applications of "<u>Embedded -</u> <u>Microcontrollers</u>"

Details

Details	
Product Status	Active
Core Processor	PIC
Core Size	16-Bit
Speed	32MHz
Connectivity	I ² C, IrDA, LINbus, SPI, UART/USART
Peripherals	Brown-out Detect/Reset, HLVD, POR, PWM, WDT
Number of I/O	17
Program Memory Size	32KB (11K x 24)
Program Memory Type	FLASH
EEPROM Size	512 x 8
RAM Size	2K x 8
Voltage - Supply (Vcc/Vdd)	2V ~ 5.5V
Data Converters	A/D 12x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Through Hole
Package / Case	20-DIP (0.300", 7.62mm)
Supplier Device Package	20-PDIP
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/pic24fv32ka301-i-p

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Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

2.0 GUIDELINES FOR GETTING STARTED WITH 16-BIT MICROCONTROLLERS

2.1 Basic Connection Requirements

Getting started with the PIC24FV32KA304 family of 16-bit microcontrollers requires attention to a minimal set of device pin connections before proceeding with development.

The following pins must always be connected:

- All VDD and Vss pins (see Section 2.2 "Power Supply Pins")
- All AVDD and AVss pins, regardless of whether or not the analog device features are used (see Section 2.2 "Power Supply Pins")
- MCLR pin (see Section 2.3 "Master Clear (MCLR) Pin")
- VCAP pins (see Section 2.4 "Voltage Regulator Pin (VCAP)")

These pins must also be connected if they are being used in the end application:

- PGECx/PGEDx pins used for In-Circuit Serial Programming[™] (ICSP[™]) and debugging purposes (see **Section 2.5 "ICSP Pins"**)
- OSCI and OSCO pins when an external oscillator source is used

(see Section 2.6 "External Oscillator Pins")

Additionally, the following pins may be required:

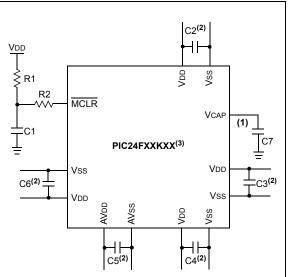
• VREF+/VREF- pins are used when external voltage reference for analog modules is implemented

Note: The AVDD and AVss pins must always be connected, regardless of whether any of the analog modules are being used.

The minimum mandatory connections are shown in Figure 2-1.

FIGURE 2-1: RECOMMENDED

MINIMUM CONNECTIONS



Key (all values are recommendations):

C1 through C6: 0.1 $\mu\text{F},$ 20V ceramic

C7: 10 µF, 16V tantalum or ceramic

R1: 10 kΩ

R2: 100Ω to 470Ω

- Note 1: See Section 2.4 "Voltage Regulator Pin (VCAP)" for explanation of VCAP pin connections.
 - 2: The example shown is for a PIC24F device with five VDD/Vss and AVDD/AVss pairs. Other devices may have more or less pairs; adjust the number of decoupling capacitors appropriately.

^{3:} Some PIC24F K parts do not have a regulator.

4.2 Data Address Space

The PIC24F core has a separate, 16-bit wide data memory space, addressable as a single linear range. The data space is accessed using two Address Generation Units (AGUs), one each for read and write operations. The data space memory map is shown in Figure 4-3.

All Effective Addresses (EAs) in the data memory space are 16 bits wide and point to bytes within the data space. This gives a data space address range of 64 Kbytes or 32K words. The lower half of the data memory space (that is, when EA<15> = 0) is used for implemented memory addresses, while the upper half (EA<15> = 1) is reserved for the Program Space Visibility (PSV) area (see Section 4.3.3 "Reading Data From Program Memory Using Program Space Visibility"). PIC24FV32KA304 family devices implement a total of 1024 words of data memory. If an EA points to a location outside of this area, an all zero word or byte will be returned.

4.2.1 DATA SPACE WIDTH

The data memory space is organized in byte-addressable, 16-bit wide blocks. Data is aligned in data memory and registers as 16-bit words, but all the data space EAs resolve to bytes. The Least Significant Bytes (LSBs) of each word have even addresses, while the Most Significant Bytes (MSBs) have odd addresses.

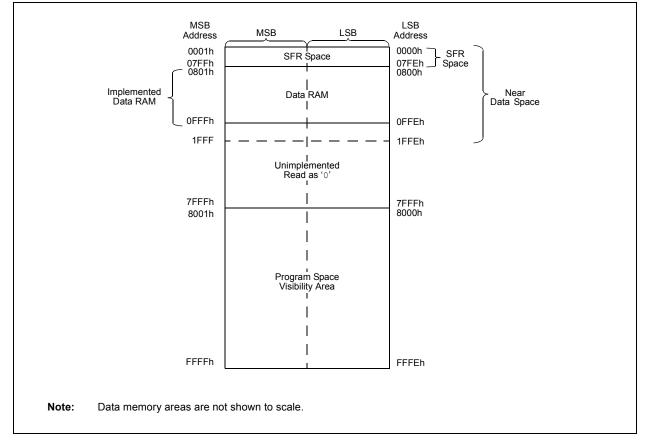


FIGURE 4-3: DATA SPACE MEMORY MAP FOR PIC24FV32KA304 FAMILY DEVICES

TABLE 4-3: CPU CORE REGISTERS MAP

IADEE -	т-∪.		OOKE															
File Name	Start Addr	Bit 15	Bit 14	Bit 13	Bit 12	Bit 11	Bit 10	Bit 9	Bit 8	Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0	All Resets
WREG0	0000		WREG0									0000						
WREG1	0002								WF	REG1								0000
WREG2	0004								WF	REG2								0000
WREG3	0006								WF	REG3								0000
WREG4	0008								WF	REG4								0000
WREG5	000A								WF	REG5								0000
WREG6	000C								WF	REG6								0000
WREG7	000E								WF	REG7								0000
WREG8	0010								WF	REG8								0000
WREG9	0012								WF	REG9								0000
WREG10	0014								WR	EG10								0000
WREG11	0016								WR	EG11								0000
WREG12	0018								WR	EG12								0000
WREG13	001A								WR	EG13								0000
WREG14	001C								WR	EG14								0000
WREG15	001E								WR	EG15								0000
SPLIM	0020								SF	PLIM								XXXX
PCL	002E								F	PCL								0000
PCH	0030	_	_	_	_	_	_	_	_	_				PCH				0000
TBLPAG	0032		_	TBLPAG							0000							
PSVPAG	0034				—	—		—	—				PS	/PAG				0000
RCOUNT	0036			RCOUNT							XXXXX							
SR	0042	_	_		DC IPL2 IPL1 IPL0 RA N OV Z C					0000								
CORCON	0044		_	IPL3 PSV 0						0000								
DISICNT	0052		_							DISIC	NT							XXXX

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Legend: — = unimplemented, read as '0'. Reset values are shown in hexadecimal.

EXAMPLE 5-2: ERASING A PROGRAM MEMORY ROW – 'C' LANGUAGE CODE

```
// C example using MPLAB C30
   int attribute ((space(auto psv))) progAddr = 0x1234; // Global variable located in Pgm Memory
   unsigned int offset;
//Set up pointer to the first memory location to be written
   TBLPAG = __builtin_tblpage(&progAddr);
                                                         // Initialize PM Page Boundary SFR
   offset = __builtin_tbloffset(&progAddr);
                                                         // Initialize lower word of address
   builtin tblwtl(offset, 0x0000);
                                                          // Set base address of erase block
                                                          // with dummy latch write
   NVMCON = 0 \times 4058;
                                                          // Initialize NVMCON
   asm("DISI #5");
                                                           // Block all interrupts for next 5
                                                           // instructions
    builtin write NVM();
                                                          // C30 function to perform unlock
                                                           // sequence and set WR
```

EXAMPLE 5-3: LOADING THE WRITE BUFFERS – ASSEMBLY LANGUAGE CODE

;	Set up NVMCO	N for row programming operatio	ns
	MOV	#0x4004, W0	;
	MOV	W0, NVMCON	; Initialize NVMCON
;	Set up a poi	nter to the first program memo	ry location to be written
;	program memo	ry selected, and writes enable	d
	MOV	#0x0000, W0	;
	MOV	W0, TBLPAG	; Initialize PM Page Boundary SFR
	MOV	#0x6000, W0	; An example program memory address
;	Perform the	TBLWT instructions to write th	e latches
;	Oth_program_		
	MOV	#LOW_WORD_0, W2	;
	MOV	#HIGH_BYTE_0, W3	;
		W2, [W0]	; Write PM low word into program latch
	TBLWTH	W3, [W0++]	; Write PM high byte into program latch
;	lst_program_		
	MOV	#LOW_WORD_1, W2	;
		#HIGH_BYTE_1, W3	;
		W2, [W0]	; Write PM low word into program latch
		W3, [W0++]	; Write PM high byte into program latch
;	2nd_program	—	
	MOV	#LOW_WORD_2, W2	;
	MOV	<pre>#HIGH_BYTE_2, W3</pre>	
		W2, [W0]	; Write PM low word into program latch
	TBLWTH	W3, [W0++]	; Write PM high byte into program latch
	•		
	•		
Ι.	-	trand	
'	32nd_program MOV		
	MOV	#LOW_WORD_31, W2 #HIGH BYTE 31, W3	;
		W2, [W0]	; ; Write PM low word into program latch
		W2, [W0] W3, [W0]	; Write PM high byte into program latch
	חואתמו	M2, [M0]	, write in high byte into program fatch

6.0 DATA EEPROM MEMORY

Note: This data sheet summarizes the features of this group of PIC24F devices. It is not intended to be a comprehensive reference source. For more information on Data EEPROM, refer to the *"PIC24F Family Reference Manual"*, Section 5. "Data EEPROM" (DS39720).

The data EEPROM memory is a Nonvolatile Memory (NVM), separate from the program and volatile data RAM. Data EEPROM memory is based on the same Flash technology as program memory, and is optimized for both long retention and a higher number of erase/write cycles.

The data EEPROM is mapped to the top of the user program memory space, with the top address at program memory address, 7FFE00h to 7FFFFFh. The size of the data EEPROM is 256 words in the PIC24FV32KA304 family devices.

The data EEPROM is organized as 16-bit wide memory. Each word is directly addressable, and is readable and writable during normal operation over the entire VDD range.

Unlike the Flash program memory, normal program execution is not stopped during a data EEPROM program or erase operation.

The data EEPROM programming operations are controlled using the three NVM Control registers:

- NVMCON: Nonvolatile Memory Control Register
- NVMKEY: Nonvolatile Memory Key Register
- NVMADR: Nonvolatile Memory Address Register

6.1 NVMCON Register

The NVMCON register (Register 6-1) is also the primary control register for data EEPROM program/erase operations. The upper byte contains the control bits used to start the program or erase cycle, and the flag bit to indicate if the operation was successfully performed. The lower byte of NVMCOM configures the type of NVM operation that will be performed.

6.2 NVMKEY Register

The NVMKEY is a write-only register that is used to prevent accidental writes or erasures of data EEPROM locations.

To start any programming or erase sequence, the following instructions must be executed first, in the exact order provided:

- 1. Write 55h to NVMKEY.
- 2. Write AAh to NVMKEY.

After this sequence, a write will be allowed to the NVMCON register for one instruction cycle. In most cases, the user will simply need to set the WR bit in the NVMCON register to start the program or erase cycle. Interrupts should be disabled during the unlock sequence.

The MPLAB® C30 C compiler provides a defined library procedure (builtin_write_NVM) to perform the unlock sequence. Example 6-1 illustrates how the unlock sequence can be performed with in-line assembly.

EXAMPLE 6-1: DATA EEPROM UNLOCK SEQUENCE

//Disable Interr	upts For 5 instruc	ctions
asm volatile ("disi #5");	
//Issue Unlock S	equence	
asm volatile ("mov #0x55, W0	\n"
"	mov W0, NVMKEY	\n"
"	mov #0xAA, W1	\n"
"	mov W1, NVMKEY	\n");
// Perform Write	/Erase operations	
asm volatile ("bset NVMCON, #WR	\n"
"	nop	\n"
"	nop	\n");

6.4.1.1 Data EEPROM Bulk Erase

To erase the entire data EEPROM (bulk erase), the address registers do not need to be configured because this operation affects the entire data EEPROM. The following sequence helps in performing a bulk erase:

- 1. Configure NVMCON to Bulk Erase mode.
- 2. Clear the NVMIF status bit and enable the NVM interrupt (optional).
- 3. Write the key sequence to NVMKEY.
- 4. Set the WR bit to begin the erase cycle.
- 5. Either poll the WR bit or wait for the NVM interrupt (NVMIF is set).

A typical bulk erase sequence is provided in Example 6-3.

6.4.2 SINGLE-WORD WRITE

To write a single word in the data EEPROM, the following sequence must be followed:

- Erase one data EEPROM word (as mentioned in the previous section) if the PGMONLY bit (NVMCON<12>) is set to '1'.
- 2. Write the data word into the data EEPROM latch.
- 3. Program the data word into the EEPROM:
 - Configure the NVMCON register to program one EEPROM word (NVMCON<5:0> = 0001xx).
 - Clear the NVMIF status bit and enable the NVM interrupt (optional).
 - Write the key sequence to NVMKEY.
 - Set the WR bit to begin the erase cycle.
 - Either poll the WR bit or wait for the NVM interrupt (NVMIF is set).
 - To get cleared, wait until NVMIF is set.

A typical single-word write sequence is provided in Example 6-4.

EXAMPLE 6-3: DATA EEPROM BULK ERASE

// Set up NVMCON to bulk erase the data EEPROM NVMCON = $0 \times 4050;$

// Disable Interrupts For 5 Instructions
asm volatile ("disi #5");

```
// Issue Unlock Sequence and Start Erase Cycle
__builtin_write_NVM();
```

EXAMPLE 6-4: SINGLE-WORD WRITE TO DATA EEPROM

```
int attribute ((space(eedata))) eeData = 0x1234;
                                                // New data to write to EEPROM
 int newData;
/*_____
                  _____
The variable eeData must be a Global variable declared outside of any method
the code following this comment can be written inside the method that will execute the write
-------
*/
  unsigned int offset;
  // Set up NVMCON to erase one word of data EEPROM
  NVMCON = 0 \times 4004;
  \ensuremath{//} Set up a pointer to the EEPROM location to be erased
  TBLPAG = __builtin_tblpage(&eeData);
                                               // Initialize EE Data page pointer
                                                // Initizlize lower word of address
  offset = __builtin_tbloffset(&eeData);
  builtin tblwtl(offset, newData);
                                                // Write EEPROM data to write latch
  asm volatile ("disi #5");
                                                 // Disable Interrupts For 5 Instructions
   builtin write NVM();
                                                 // Issue Unlock Sequence & Start Write Cycle
  while (NVMCONbits.WR=1);
                                                 // Optional: Poll WR bit to wait for
                                                 // write sequence to complete
```

R/W-0, HS	S R/W-0, HS	R/W-0	R/W-0	U-0	R/C-0, HS	R/W-0	R/W-0		
TRAPR	IOPUWR	SBOREN	RETEN ⁽³⁾	—	DPSLP	CM	PMSLP		
bit 15							bit 8		
R/W-0, H	S R/W-0, HS	R/W-0, HS	R/W-0, HS	R/W-0, HS	R/W-0, HS	R/W-1, HS	R/W-1, HS		
EXTR	SWR	SWDTEN ⁽²⁾	WDTO	SLEEP	IDLE	BOR	POR		
bit 7							bit 0		
		<u> </u>			<u> </u>				
Legend:		C = Clearable			re Settable bit				
R = Reada		W = Writable b	bit	•	nented bit, read	as '0'			
-n = Value	at POR	'1' = Bit is set		'0' = Bit is cle	ared	x = Bit is unkn	iown		
bit 15	TRAPR: Tran	Reset Flag bit							
	=	onflict Reset has	occurred						
		onflict Reset has							
bit 14	IOPUWR: Ille	gal Opcode or l	Jninitialized W	Access Reset	Flag bit				
	1 = An illegal Pointer c	l opcode detecti aused a Reset	on, an illegal a	ddress mode o	or Uninitialized V	V register used	as an Address		
	0 = An illegal	I opcode or Unir	nitialized W Re	set has not oc	curred				
bit 13	SBOREN: So	oftware Enable/E	Disable of BOF	R bit					
		1 = BOR is turned on in software 0 = BOR is turned off in software							
bit 12	RETEN: Rete	ention Sleep Mo	de control bit ⁽³	6)					
		d voltage supply							
bit 11	Unimplemen	ted: Read as '0	3						
bit 10	DPSLP: Deep	p Sleep Mode F	lag bit						
	•	ep has occurred ep has not occu							
bit 9	CM: Configur	ation Word Misr	natch Reset F	lag bit					
	Ų	uration Word Mis uration Word Mis			ed				
bit 8	PMSLP: Proc	gram Memory Po	ower During S	leep bit					
		memory bias vo memory bias v mode				the Voltage Re	gulator enters		
bit 7	-	nal Reset (MCLF	R) Pin bit						
Sit 7	1 = A Master	Clear (pin) Reso Clear (pin) Reso	et has occurre						
bit 6		ire Reset (Instru							
	1 = A reset	instruction has I instruction has I	peen executed						
Note 1:	All of the Reset a cause a device		be set or clear	ed in software.	Setting one of the	nese bits in soft	ware does not		
2:	If the FWDTEN SWDTEN bit se	x Configuration I	bit is '1' (unpro	ogrammed), the	e WDT is always	enabled regar	dless of the		
3:	This is implement	-	V32KA3XX pa	arts only; not us	sed on PIC24F3	2KA3XX device	es.		

REGISTER 7-1: RCON: RESET CONTROL REGISTER⁽¹⁾

R/W-0	R/W-0	R/W-0	R/W-0	R/W-0	U-0	R/W-0	U-0			
U2TXIE	U2RXIE	INT2IE	T5IE	T4IE		OC3IE				
bit 15	1						bit 8			
U-0	U-0	U-0	R/W-0	R/W-0	R/W-0	R/W-0	R/W-0			
_	—		INT1IE	CNIE	CMIE	MI2C1IE	SI2C1IE			
bit 7							bit (
Legend:										
R = Readable	e bit	W = Writable	bit	U = Unimplem	nented bit, read	d as '0'				
-n = Value at	POR	'1' = Bit is set		'0' = Bit is clea		x = Bit is unkn	own			
bit 15	U2TXIE: UAR	RT2 Transmitter	Interrupt Ena	ble bit						
		equest is enab								
	•	equest is not e								
bit 14		RT2 Receiver Ir	•	e bit						
	•	equest is enab								
h it 40		equest is not e								
bit 13		nal Interrupt 2 equest is enab								
		equest is enab								
bit 12		Interrupt Enabl								
		equest is enab								
		equest is not e								
bit 11	T4IE: Timer4	Fimer4 Interrupt Enable bit								
	•	equest is enab								
	-	equest is not e								
bit 10	-	ted: Read as '								
bit 9	-	ut Compare 3 Ir	-	e bit						
		equest is enab								
bit 8-5	-	equest is not e ted: Read as '								
bit 4	-	nal Interrupt 1								
		request is enab								
		request is not e								
bit 3	CNIE: Input C	Change Notifica	tion Interrupt	Enable bit						
	-	equest is enab	=							
	0 = Interrupt r	equest is not e	nabled							
bit 2	CMIE: Compa	arator Interrupt	Enable bit							
	•	equest is enab								
		equest is not e								
bit 1		ster I2C1 Even	-	able bit						
	•	equest is enab								
hit 0		equest is not e		lo hit						
bit 0		ve I2C1 Event I								
	⊥ – menupt r	equest is enab	nabled							

REGISTER 8-12: IEC1: INTERRUPT ENABLE CONTROL REGISTER 1

REGISTER 8-30: IPC18: INTERRUPT PRIORITY CONTROL REGISTER 18

U-0	U-0	U-0	U-0	U-0	U-0	U-0	U-0
—	—	—	—	—	_		—
bit 15							bit 8
U-0	U-0	U-0	U-0	U-0	R/W-1	R/W-0	R/W-0
_	_	_	_	_	HLVDIP2	HLVDIP1	HLVDIP0

bit 7

Legend:			
R = Readable bit	W = Writable bit	U = Unimplemented bit	t, read as '0'
-n = Value at POR	'1' = Bit is set	'0' = Bit is cleared	x = Bit is unknown

bit 15-3 Unimplemented: Read as '0'

REGISTER 8-31: IPC19: INTERRUPT PRIORITY CONTROL REGISTER 19

U-0	U-0	U-0	U-0	U-0	U-0	U-0	U-0
_	—	—	—	—			—
bit 15							bit 8

U-0	R/W-1	R/W-0	R/W-0	U-0	U-0	U-0	U-0
—	CTMUIP2	CTMUIP1	CTMUIP0	—	—	—	—
bit 7							bit 0

Legend:			
R = Readable bit	W = Writable bit	U = Unimplemented bit, read	d as '0'
-n = Value at POR	'1' = Bit is set	'0' = Bit is cleared	x = Bit is unknown

bit 15-7 Unimplemented: Read as '0'

bit 6-4 **CTMUIP<2:0>:** CTMU Interrupt Priority bits

111 = Interrupt is Priority 7 (highest priority interrupt)

•

001 = Interrupt is Priority 1

000 = Interrupt source is disabled

bit 3-0 Unimplemented: Read as '0'

•

bit 0

NOTES:

10.0 POWER-SAVING FEATURES

Note:	This data sheet summarizes the features of this group of PIC24F devices. It is not						
	intended to be a comprehensive refer-						
	ence source. For more information, refer						
	to the "PIC24F Family Reference						
	Manual", "Section 39. Power-Saving						
	Features with Deep Sleep" (DS39727).						

The PIC24FV32KA304 family of devices provides the ability to manage power consumption by selectively managing clocking to the CPU and the peripherals. In general, a lower clock frequency and a reduction in the number of circuits being clocked constitutes lower consumed power. All PIC24F devices manage power consumption in four different ways:

- Clock Frequency
- Instruction-Based Sleep, Idle and Deep Sleep modes
- · Software Controlled Doze mode
- Selective Peripheral Control in Software

Combinations of these methods can be used to selectively tailor an application's power consumption, while still maintaining critical application features, such as timing-sensitive communications.

10.1 Clock Frequency and Clock Switching

PIC24F devices allow for a wide range of clock frequencies to be selected under application control. If the system clock configuration is not locked, users can choose low-power or high-precision oscillators by simply changing the NOSCx bits. The process of changing a system clock during operation, as well as limitations to the process, are discussed in more detail in **Section 9.0** "Oscillator Configuration".

10.2 Instruction-Based Power-Saving Modes

PIC24F devices have two special power-saving modes that are entered through the execution of a special PWRSAV instruction. Sleep mode stops clock operation and halts all code execution; Idle mode halts the CPU and code execution, but allows peripheral modules to continue operation. Deep Sleep mode stops clock operation, code execution and all peripherals, except RTCC and DSWDT. It also freezes I/O states and removes power to SRAM and Flash memory. The assembly syntax of the PWRSAV instruction is shown in Example 10-1.

Note: SLEEP_MODE and IDLE_MODE are constants defined in the assembler include file for the selected device.

Sleep and Idle modes can be exited as a result of an enabled interrupt, WDT time-out or a device Reset. When the device exits these modes, it is said to "wake-up".

10.2.1 SLEEP MODE

Sleep mode includes these features:

- The system clock source is shut down. If an on-chip oscillator is used, it is turned off.
- The device current consumption will be reduced to a minimum provided that no I/O pin is sourcing current.
- The I/O pin directions and states are frozen.
- The Fail-Safe Clock Monitor does not operate during Sleep mode since the system clock source is disabled.
- The LPRC clock will continue to run in Sleep mode if the WDT or RTCC with LPRC as the clock source is enabled.
- The WDT, if enabled, is automatically cleared prior to entering Sleep mode.
- Some device features or peripherals may continue to operate in Sleep mode. This includes items, such as the Input Change Notification on the I/O ports, or peripherals that use an external clock input. Any peripheral that requires the system clock source for its operation will be disabled in Sleep mode.

The device will wake-up from Sleep mode on any of these events:

- On any interrupt source that is individually enabled
- · On any form of device Reset
- · On a WDT time-out

On wake-up from Sleep, the processor will restart with the same clock source that was active when Sleep mode was entered.

EXAMPLE 10-1: PWRSAV INSTRUCTION SYNTAX

PWRSAV	#SLEEP_MODE	;	Put the device into SLEEP mode
PWRSAV	#IDLE_MODE	;	Put the device into IDLE mode
BSET	DSCON, #DSEN	;	Enable Deep Sleep
PWRSAV	#SLEEP_MODE	;	Put the device into Deep SLEEP mode

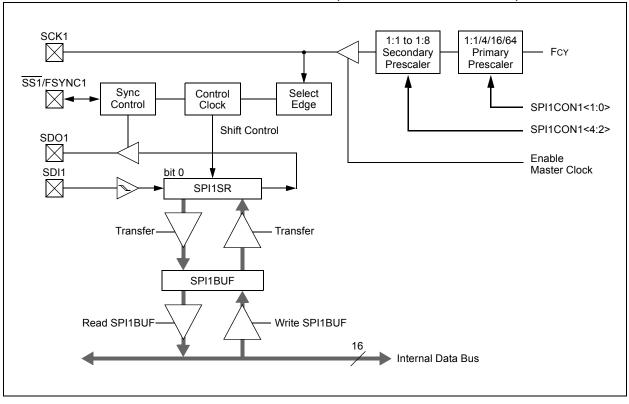


FIGURE 16-1: SPI1 MODULE BLOCK DIAGRAM (STANDARD BUFFER MODE)

REGISTER 18-2: UxSTA: UARTx STATUS AND CONTROL REGISTER (CONTINUED)

bit 5	ADDEN: Address Character Detect bit (bit 8 of received data = 1)
	 1 = Address Detect mode is enabled; if 9-bit mode is not selected, this does not take effect 0 = Address Detect mode is disabled
bit 4	RIDLE: Receiver Idle bit (read-only)
	1 = Receiver is Idle0 = Receiver is active
bit 3	PERR: Parity Error Status bit (read-only)
	 1 = Parity error has been detected for the current character (character at the top of the receive FIFO) 0 = Parity error has not been detected
bit 2	FERR: Framing Error Status bit (read-only)
	 1 = Framing error has been detected for the current character (character at the top of the receive FIFO) 0 = Framing error has not been detected
bit 1	OERR: Receive Buffer Overrun Error Status bit (clear/read-only)
	1 = Receive buffer has overflowed
	0 = Receive buffer has not overflowed (clearing a previously set OERR bit (1 \rightarrow 0 transition) will reset the receiver buffer and the RSR to the empty state)
bit 0	URXDA: UARTx Receive Buffer Data Available bit (read-only)
	 1 = Receive buffer has data; at least one more characters can be read 0 = Receive buffer is empty

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19.2 RTCC Module Registers

The RTCC module registers are organized into three categories:

- RTCC Control Registers
- RTCC Value Registers
- Alarm Value Registers

19.2.1 REGISTER MAPPING

To limit the register interface, the RTCC Timer and Alarm Time registers are accessed through corresponding register pointers. The RTCC Value Register Window (RTCVALH and RTCVALL) uses the RTCPTR bits (RCFGCAL<9:8>) to select the desired Timer register pair (see Table 19-1).

By writing the RTCVALH byte, the RTCC Pointer value, the RTCPTR<1:0> bits decrement by one until they reach '00'. Once they reach '00', the MINUTES and SECONDS value will be accessible through RTCVALH and RTCVALL until the pointer value is manually changed.

TABLE 19-1: RTCVAL REGISTER MAPPING

RTCPTR<1:0>	RTCC Value Register Window				
RICPIRSI.02	RTCVAL<15:8>	RTCVAL<7:0>			
00	MINUTES	SECONDS			
01	WEEKDAY	HOURS			
10	MONTH	DAY			
11	—	YEAR			

The Alarm Value Register Window (ALRMVALH and ALRMVALL) uses the ALRMPTRx bits (ALCFGRPT<9:8>) to select the desired Alarm register pair (see Table 19-2).

By writing the ALRMVALH byte, the Alarm Pointer value (ALRMPTR<1:0> bits) decrements by one until they reach '00'. Once they reach '00', the ALRMMIN and ALRMSEC value will be accessible through ALRMVALH and ALRMVALL, until the pointer value is manually changed.

TABLE 19-2: ALRMVAL REGISTER MAPPING

ALRMPTR	Alarm Value Register Window				
<1:0>	ALRMVAL<15:8>	ALRMVAL<7:0>			
00	ALRMMIN	ALRMSEC			
01	ALRMWD	ALRMHR			
10	ALRMMNTH	ALRMDAY			
11	PWCSTAB	PWCSAMP			

Considering that the 16-bit core does not distinguish between 8-bit and 16-bit read operations, the user must be aware that when reading either the ALRMVALH or ALRMVALL bytes, the ALRMPTR<1:0> value will be decremented. The same applies to the RTCVALH or RTCVALL bytes with the RTCPTR<1:0> being decremented.

Note:	This only applies to read operations and
	not write operations.

19.2.2 WRITE LOCK

In order to perform a write to any of the RTCC Timer registers, the RTCWREN bit (RTCPWC<13>) must be set (see Example 19-1).

Note: To avoid accidental writes to the timer, it is recommended that the RTCWREN bit (RCFGCAL<13>) is kept clear at any other time. For the RTCWREN bit to be set, there is only one instruction cycle time window allowed between the 55h/AA sequence and the setting of RTCWREN. Therefore, it is recommended that code follow the procedure in Example 19-1.

19.2.3 SELECTING RTCC CLOCK SOURCE

There are four reference source clock options that can be selected for the RTCC using the RTCCSEL<1:0> bits: 00 = Secondary Oscillator, 01 = LPRC, 10 = 50 Hz External Clock and 11 = 60 Hz External Clock.

asm	volatile	("push w7");
asm	volatile	("push w8");
asm	volatile	("disi #5");
asm	volatile	("mov #0x55, w7");
asm	volatile	("mov w7, NVMKEY");
asm	volatile	("mov #0xAA, w8");
asm	volatile	("mov w8, NVMKEY");
asm	volatile	("bset RCFGCAL, #13"); //set the RTCWREN bit
asm	volatile	("pop w8");
asm	volatile	("pop w7");

TABLE 28-2: INSTRUCTION SET OVERVIEW (CONTINUED)

Assembly Mnemonic		Assembly Syntax	Description	# of Words	# of Cycles	Status Flags Affected
PWRSAV	PWRSAV	#lit1	Go into Sleep or Idle mode	1	1	WDTO, Sleep
RCALL	RCALL	Expr	Relative Call	1	2	None
	RCALL	Wn	Computed Call	1	2	None
REPEAT	REPEAT	#lit14	Repeat Next Instruction lit14 + 1 times	1	1	None
	REPEAT	Wn	Repeat Next Instruction (Wn) + 1 times	1	1	None
RESET	RESET		Software Device Reset	1	1	None
RETFIE	RETFIE		Return from Interrupt	1	3 (2)	None
RETLW	RETLW	#lit10,Wn	Return with Literal in Wn	1	3 (2)	None
RETURN	RETURN		Return from Subroutine	1	3 (2)	None
RLC	RLC	f	f = Rotate Left through Carry f	1	1	C, N, Z
	RLC	f,WREG	WREG = Rotate Left through Carry f	1	1	C, N, Z
	RLC	Ws,Wd	Wd = Rotate Left through Carry Ws	1	1	C, N, Z
RLNC	RLNC	f	f = Rotate Left (No Carry) f	1	1	N, Z
	RLNC	f,WREG	WREG = Rotate Left (No Carry) f	1	1	N, Z
	RLNC	Ws,Wd	Wd = Rotate Left (No Carry) Ws	1	1	N, Z
RRC	RRC	f	f = Rotate Right through Carry f	1	1	C, N, Z
	RRC	f,WREG	WREG = Rotate Right through Carry f	1	1	C, N, Z
	RRC	Ws,Wd	Wd = Rotate Right through Carry Ws	1	1	C, N, Z
RRNC	RRNC	f	f = Rotate Right (No Carry) f	1	1	N, Z
	RRNC	f,WREG	WREG = Rotate Right (No Carry) f	1	1	N, Z
	RRNC	Ws,Wd	Wd = Rotate Right (No Carry) Ws	1	1	N, Z
SE	SE	Ws,Wnd	Wnd = Sign-Extended Ws	1	1	C, N, Z
SETM	SETM	f	f = FFFFh	1	1	None
	SETM	WREG	WREG = FFFFh	1	1	None
	SETM	Ws	Ws = FFFFh	1	1	None
SL	SL	f	f = Left Shift f	1	1	C, N, OV, Z
	SL	f,WREG	WREG = Left Shift f	1	1	C, N, OV, Z
	SL	Ws,Wd	Wd = Left Shift Ws	1	1	C, N, OV, Z
	SL	Wb,Wns,Wnd	Wnd = Left Shift Wb by Wns	1	1	N, Z
	SL	Wb,#lit5,Wnd	Wnd = Left Shift Wb by lit5	1	1	N, Z
SUB	SUB	f	f = f – WREG	1	1	C, DC, N, OV, Z
	SUB	f,WREG	WREG = f – WREG	1	1	C, DC, N, OV, Z
	SUB	#lit10,Wn	Wn = Wn – lit10	1	1	C, DC, N, OV, Z
	SUB	Wb,Ws,Wd	Wd = Wb – Ws	1	1	C, DC, N, OV, Z
	SUB	Wb,#lit5,Wd	Wd = Wb – lit5	1	1	C, DC, N, OV, Z
SUBB	SUBB	f	$f = f - WREG - (\overline{C})$	1	1	C, DC, N, OV, Z
	SUBB	f,WREG	WREG = $f - WREG - (\overline{C})$	1	1	C, DC, N, OV, Z
	SUBB	#lit10,Wn	$Wn = Wn - lit10 - (\overline{C})$	1	1	C, DC, N, OV, Z
	SUBB	Wb,Ws,Wd	$Wd = Wb - Ws - (\overline{C})$	1	1	C, DC, N, OV, Z
	SUBB	Wb,#lit5,Wd	$Wd = Wb - lit5 - (\overline{C})$	1	1	C, DC, N, OV, Z
SUBR	SUBR	f	f = WREG – f	1	1	C, DC, N, OV, Z
	SUBR	f,WREG	WREG = WREG – f	1	1	C, DC, N, OV, Z
	SUBR	Wb,Ws,Wd	Wd = Ws – Wb	1	1	C, DC, N, OV, Z
	SUBR	Wb,#lit5,Wd	Wd = lit5 – Wb	1	1	C, DC, N, OV, Z
SUBBR	SUBBR	f	$f = WREG - f - (\overline{C})$	1	1	C, DC, N, OV, Z
	SUBBR	f,WREG	$WREG = WREG - f - (\overline{C})$	1	1	C, DC, N, OV, Z
	SUBBR		$Wd = Ws - Wb - (\overline{C})$	1	1	C, DC, N, OV, Z
		Wb,Ws,Wd				
CHA D	SUBBR	Wb,#lit5,Wd	Wd = lit5 – Wb – (C)	1	1	C, DC, N, OV, Z
SWAP	SWAP.b	Wn	Wn = Nibble Swap Wn	1	1	None
	SWAP	Wn	Wn = Byte Swap Wn	1	1	None
TBLRDH	TBLRDH	Ws,Wd	Read Prog<23:16> to Wd<7:0>	1	2	None

Assembly Mnemonic		Assembly Syntax	Description	# of Words	# of Cycles	Status Flags Affected
TBLRDL	TBLRDL	Ws,Wd	Read Prog<15:0> to Wd	1	2	None
TBLWTH	TBLWTH	Ws,Wd	Write Ws<7:0> to Prog<23:16>	1	2	None
TBLWTL	TBLWTL	Ws,Wd	Write Ws to Prog<15:0>	1	2	None
ULNK	ULNK		Unlink Frame Pointer	1	1	None
XOR	XOR	f	f = f .XOR. WREG	1	1	N, Z
	XOR	f,WREG	WREG = f .XOR. WREG	1	1	N, Z
	XOR	#lit10,Wn	Wd = lit10 .XOR. Wd	1	1	N, Z
	XOR	Wb,Ws,Wd	Wd = Wb .XOR. Ws	1	1	N, Z
	XOR	Wb,#lit5,Wd	Wd = Wb .XOR. lit5	1	1	N, Z
ZE	ZE	Ws,Wnd	Wnd = Zero-Extend Ws	1	1	C, Z, N

TABLE 28-2: INSTRUCTION SET OVERVIEW (CONTINUED)

TABLE 29-1: THERMAL OPERATING CONDITIONS

Rating	Symbol	Min	Тур	Max	Unit
Operating Junction Temperature Range	TJ	-40	_	+140	°C
Operating Ambient Temperature Range	TA	-40		+125	°C
Power Dissipation: Internal Chip Power Dissipation: $PINT = VDD x (IDD - \Sigma IOH)$ I/O Pin Power Dissipation: $PI/O = \Sigma (\{VDD - VOH\} x IOH) + \Sigma (VOL x IOL)$	PD	PINT + PI/O		W	
Maximum Allowed Power Dissipation	PDMAX	(TJ — ΤΑ)/θJ	JA	W

TABLE 29-2: THERMAL PACKAGING CHARACTERISTICS

Characteristic	Symbol	Тур	Max	Unit	Notes
Package Thermal Resistance, 20-Pin SPDIP	θJA	62.4	_	°C/W	1
Package Thermal Resistance, 28-Pin SPDIP	θJA	60	_	°C/W	1
Package Thermal Resistance, 20-Pin SSOP	θJA	108	—	°C/W	1
Package Thermal Resistance, 28-Pin SSOP	θJA	71	_	°C/W	1
Package Thermal Resistance, 20-Pin SOIC	θJA	75	_	°C/W	1
Package Thermal Resistance, 28-Pin SOIC	θJA	80.2	_	°C/W	1
Package Thermal Resistance, 28-Pin QFN	θJA	32	_	°C/W	1
Package Thermal Resistance, 44-Pin QFN	θJA	29	_	°C/W	1
Package Thermal Resistance, 48-Pin UQFN	θJA	_	_	°C/W	1

Note 1: Junction to ambient thermal resistance, Theta-JA (θ JA) numbers are achieved by package simulations.

TABLE 29-3: DC CHARACTERISTICS: TEMPERATURE AND VOLTAGE SPECIFICATIONS

DC CHARACTERISTICS			$\begin{array}{llllllllllllllllllllllllllllllllllll$						
Param No.	Symbol	Characteristic	Min	Typ ⁽¹⁾	Max	Units	Conditions		
DC10	Vdd	Supply Voltage	1.8	_	3.6	V	For F devices		
			2.0		5.5	V	For FV devices		
DC12 V	Vdr	RAM Data Retention Voltage ⁽²⁾	1.5		_	V	For F devices		
			1.7		_	V	For FV devices		
DC16	VPOR	VDD Start Voltage to Ensure Internal Power-on Reset Signal	Vss	—	0.7	V			
DC17	SVDD	VDD Rise Rate to Ensure Internal Power-on Reset Signal	0.05	—	_	V/ms	0-3.3V in 0.1s 0-2.5V in 60 ms		

Note 1: Data in "Typ" column is at 3.3V, +25°C unless otherwise stated. Parameters are for design guidance only and are not tested.

2: This is the limit to which VDD can be lowered without losing RAM data.

DC CHARACTERISTICS		$ \begin{array}{llllllllllllllllllllllllllllllllllll$							
Parameter No.	Device	Typical ⁽¹⁾	Max	Units	Conditions				
Module Diffe	erential Current (∆IPD) ⁽³⁾							
DC78	PIC24FV32KA3XX	0.03	_	μA	-40°C	2.0V			
		0.05	0.20	μA	+85°C	5.0V			
			0.30	μA	+125°C	5.0V	Deep Sleep BOR:		
	PIC24F32KA3XX	0.03	_	μA	-40°C	1.8V	Δ ILPBOR ⁽⁵⁾		
		0.05	0.20	μA	+85°C	3.3V			
		_	0.30	μA	+125°C	3.3V			
DC80	PIC24FV32KA3XX	0.20	_	μA	-40°C	2.0V			
		0.70	1.5	μA	+85°C	5.0V			
		_	1.5	μA	+125°C	5.0V	Deep Sleep WDT:		
	PIC24F32KA3XX	0.20		μA	-40°C	1.8V	∆ldswdt (LPRC) ⁽⁶⁾		
		0.35	0.8	μA	+85°C	3.3V			
		_	1.5	μA	+125°C	3.3V			

TABLE 29-8: DC CHARACTERISTICS: POWER-DOWN CURRENT (IPD) (CONTINUED)

Legend: Unshaded rows represent PIC24F32KA3XX devices and shaded rows represent PIC24FV32KA3XX devices. Note 1: Data in the Typical column is at 3.3V, +25°C (PIC24F32KA3XX) or 5.0V, +25°C (PIC24FV32KA3XX) unless

otherwise stated. Parameters are for design guidance only and are not tested.

Base IPD is measured with all peripherals and clocks shut down. All I/Os are configured as outputs and set low, 2: PMSLP is set to '0' and WDT, etc., are all switched off.

3: The Δ current is the additional current consumed when the module is enabled. This current should be added to the base IPD current.

4: This current applies to Sleep only.

5: This current applies to Sleep and Deep Sleep.6: This current applies to Deep Sleep only.

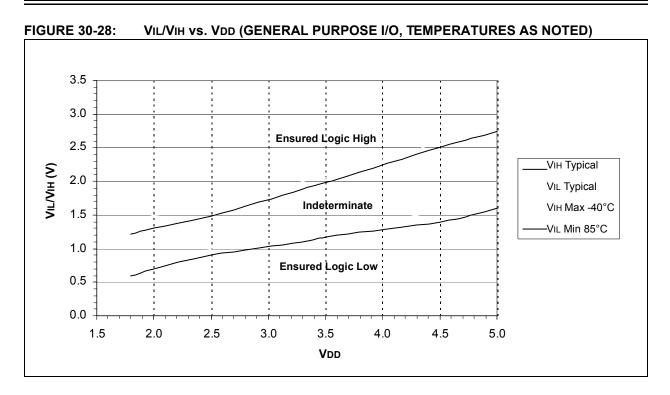
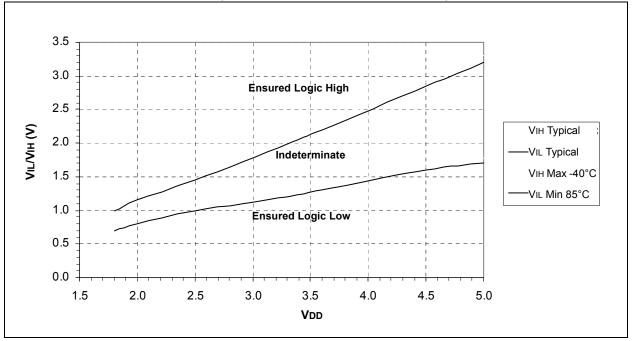
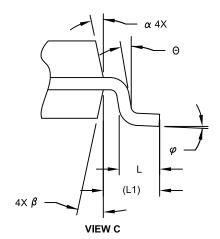


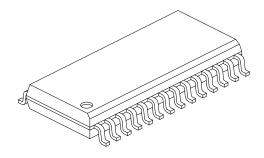
FIGURE 30-29: VIL/VIH vs. VDD (I²C[™], TEMPERATURES AS NOTED)



28-Lead Plastic Small Outline (SO) - Wide, 7.50 mm Body [SOIC]

Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging





	MILLIMETERS					
Dimension	Limits	MIN	NOM	MAX		
Number of Pins	N	28				
Pitch	е	1.27 BSC				
Overall Height	Α	-	-	2.65		
Molded Package Thickness	A2	2.05	-	-		
Standoff §	A1	0.10	-	0.30		
Overall Width	E	10.30 BSC				
Molded Package Width	E1	7.50 BSC				
Overall Length	D	17.90 BSC				
Chamfer (Optional)	h	0.25	-	0.75		
Foot Length	L	0.40 -		1.27		
Footprint	L1	1.40 REF				
Lead Angle	Θ	0°	-	-		
Foot Angle	φ	0°	-	8°		
Lead Thickness	С	0.18	-	0.33		
Lead Width	b	0.31	-	0.51		
Mold Draft Angle Top	α	5°	-	15°		
Mold Draft Angle Bottom	β	5°	-	15°		

Notes:

- 1. Pin 1 visual index feature may vary, but must be located within the hatched area.
- 2. § Significant Characteristic
- Dimension D does not include mold flash, protrusions or gate burrs, which shall not exceed 0.15 mm per end. Dimension E1 does not include interlead flash or protrusion, which shall not exceed 0.25 mm per side.
- 4. Dimensioning and tolerancing per ASME Y14.5M
 - BSC: Basic Dimension. Theoretically exact value shown without tolerances. REF: Reference Dimension, usually without tolerance, for information purposes only.
- 5. Datums A & B to be determined at Datum H.

Microchip Technology Drawing C04-052C Sheet 2 of 2